has a larger number of the emitter electrodes than the first heterojunction bipolar transistors.

8. The high-frequency semiconductor device of claim **7**, wherein each first heterojunction bipolar transistor has a single emitter electrode and each second heterojunction bipolar transistor has two emitter electrodes.

9. The high-frequency semiconductor device according to claim **1**, wherein the output amplifier has an output port connected to the collector electrodes of each of the second heterojunction bipolar transistors.

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